

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-14 Cancelled

15. (currently amended) A semiconductor processing chamber, comprising:

a top electrode in communication with a power supply; and

a processing chamber defined within a base, a sidewall extending from the base, and a continuous top disposed on the sidewall, the top electrode disposed over and isolated from the processing chamber and the top of the processing chamber being a window allowing energy from the top electrode to pass therethrough, the processing chamber having an outlet enabling removal of fluids within the processing chamber, the processing chamber including,

a substrate support; and

an inner surface of the processing chamber defined by the base, the sidewall and the top, the inner surface being coated with a removable silicon containing coating prior to a processing operation, ~~the silicon containing coating configured to seal particles between the inner surface and the silicon containing coating;~~ and

an outer surface of the substrate support coated with the removable silicon containing coating, wherein the silicon containing coating prevents

transfer of metal contaminants from the inner surface of the chamber to a wafer during a processing operation.

16. cancelled

17. (currently amended) The semiconductor processing chamber of claim 15, wherein the silicon containing coating has a thickness of between about 50 angstroms (Å) and about 4000Å.

18. cancelled

19. (currently amended) The semiconductor processing chamber of claim 15, wherein the base, and the sidewall are formed from the group consisting of aluminum, ceramic, aluminum coated with ceramic, and aluminum coated with silicon carbide ~~the silicon containing coating is removed and reapplied after completion of each process operation within the semiconductor processing chamber.~~

20. (new) The semiconductor processing chamber of claim 15, wherein the window is composed of one of sapphire or quartz.

21. (new) The semiconductor processing chamber of claim 15, wherein the substrate support is an electrostatic chuck.

22. (new) The semiconductor processing chamber of claim 1, wherein the substrate support is in communication with a substrate support power supply.

23. (new) The semiconductor processing chamber of claim 1, wherein the silicon containing coating is composed of silicon, oxygen and chlorine.

24. (new) The semiconductor processing chamber of claim 1, wherein the silicon containing coating is composed of silicon, oxygen and fluorine.

25. (new) The semiconductor processing chamber of claim 1, wherein the silicon containing coating is composed of silicon, oxygen and bromine.